Abstract Submitted
for the MAR12 Meeting of
The American Physical Society

Transport in graphene-boron nitride heterostructures FRANCOIS AMET, ANDREI GARCIA, JAMES WILLIAMS, DAVID GOLDHABER-GORDON, Stanford University — Transferring graphene on hexagonal boron nitride permits the fabrication of high mobility graphene devices. We report on in-plane transport measurements on dual gated graphene systems using boron nitride as a substrate. The low amount of disorder allows for ballistic effects to be probed, as we can gate-define regions narrower than the mean free path. This work is supported by the Center on Functional Engineered Nano-Architectonics.

Francois Amet
Stanford University

Date submitted: 11 Nov 2011 Electronic form version 1.4